

Thyristor Module

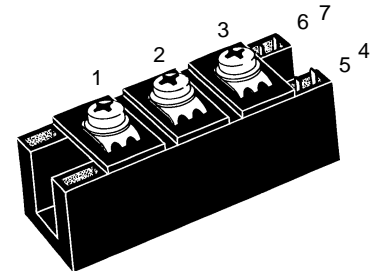
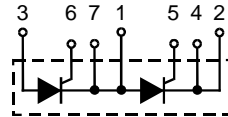
Preliminary data

$$I_{TRMS} = 2 \times 300 \text{ A}$$

$$I_{TAVM} = 2 \times 128 \text{ A}$$

$$V_{RRM, DRM} = 800-1800 \text{ V}$$

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
V	V	
900	800	MCC 122-08io1
1300	1200	MCC 122-12io1
1500	1400	MCC 122-14io1
1700	1600	MCC 122-16io1
1900	1800	MCC 122-18io1



Symbol	Conditions	Maximum Ratings	
I_{TRMS}		300	A
I_{TAVM}	$T_C = 85^\circ\text{C}$; 180° sine	128	A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	3600 3850 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	3200 3420 A
I^2dt	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	64800 62300 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	51200 49100 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ f = 50Hz, $t_p = 200\mu\text{s}$ $V_D = \frac{2}{3} V_{DRM}$ $I_G = 0.5 \text{ A}$ $di_G/dt = 0.5 \text{ A}/\mu\text{s}$	repetitive, $I_T = 500 \text{ A}$	150 A/ μs
		non repetitive, $I_T = 500 \text{ A}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = \frac{2}{3} V_{DRM}$	1000 V/ μs
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$ $t_p = 500 \mu\text{s}$	120 60 W
			8 W
P_{GAV}			8 W
V_{RGM}			10 V
T_{VJ}			-40...+125 °C
T_{VJM}			125 °C
T_{stg}			-40...+125 °C
V_{ISOL}	50/60 Hz, RMS	t = 1 min	3000 V~
	$I_{ISOL} \leq 1 \text{ mA}$	t = 1 s	3600 V~
M_d	Mounting torque (M6)		2.25-2.75/20-25 Nm/lb.in.
	Terminal connection torque (M6)		4.5-5.5/40-48 Nm/lb.in.
Weight	Typical including screws		125 g

Features

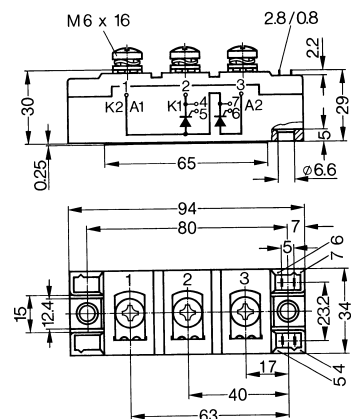
- International standard package
- Direct copper bonded Al_2O_3 -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 72873
- Keyed gate/cathode twin pins

Applications

- Motor control
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Contactless switches

Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Dimensions in mm (1 mm = 0.0394")


Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

Symbol	Conditions	Characteristic Values	
I_{RRM}, I_{DRM}	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	10	mA
V_T, V_F	$I_T, I_F = 120 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.13	V
V_{T0}	$T_{VJ} = 125^\circ\text{C}$; For power-loss calculations only	0.85	V
r_T	$T_{VJ} = T_{VJM}$	2	m Ω
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	1.4	V
	$T_{VJ} = -40^\circ\text{C}$	1.6	V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	150	mA
	$T_{VJ} = -40^\circ\text{C}$	200	mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	0.2	V
I_{GD}		10	mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}, V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	300	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	2	μs
t_q	$T_{VJ} = T_{VJM}; I_T = 120 \text{ A}, t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s typ.}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = \frac{2}{3} V_{DRM}$	150	μs
Q_S	$T_{VJ} = T_{VJM}; I_T, I_F = 200 \text{ A}, -di/dt = 50 \text{ A}/\mu\text{s}$	330	μC
I_{RM}		180	A
R_{thJC}	per thyristor/diode; DC current	0.2	K/W
	per module	0.1	K/W
R_{thCH}	per thyristor/diode; DC current	typ. 0.1	K/W
d_s	Creepage distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red

Type **ZY 180L** (L = Left for pin pair 4/5) } UL Styles 1385,
 Type **ZY 180R** (R = right for pin pair 6/7) } CSA Class 5851, File 41234